

isc Silicon PNP Darlington Power Transistor

2STW200

DESCRIPTION

- With TO-3PN packaging
- Very high DC current gain
- Monolithic darlington transistor with integrated antiparallel collector-emitter diode
- Complement to Type 2STW100
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

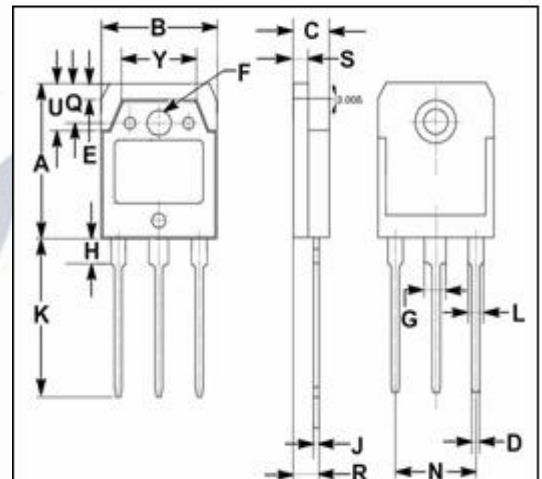
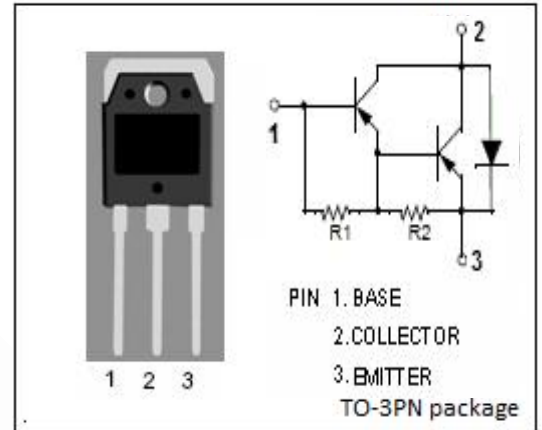
- AC-DC motor control
- Electronic ignition
- Alternator regulator

ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|------------------------------|---------|------|
| V _{CBO} | Collector-Base Voltage | -80 | V |
| V _{CEO} | Collector-Emitter Voltage | -80 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _c | Collector Current-Continuous | -25 | A |
| I _{CM} | Collector Current-Peak | -40 | A |
| I _B | Base Current | -6 | A |
| P _C | Collector Power Dissipation | 130 | W |
| T _j | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature Range | -65~150 | °C |

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | MAX | UNIT |
|---------------------|----------------------------------------|------|------|
| R _{th j-c} | Thermal Resistance,Junction to Case | 0.96 | °C/W |
| R _{th j-a} | Thermal Resistance,Junction to Ambient | 62.5 | °C/W |



| DIM | mm | |
|-----|-------|-------|
| | MIN | MAX |
| A | 19.60 | 20.30 |
| B | 15.50 | 15.70 |
| C | 4.70 | 4.90 |
| D | 0.90 | 1.10 |
| E | 1.90 | 2.10 |
| F | 3.40 | 3.60 |
| G | 2.90 | 3.20 |
| H | 3.20 | 3.40 |
| J | 0.595 | 0.605 |
| K | 19.80 | 20.70 |
| L | 1.90 | 2.20 |
| N | 10.89 | 10.91 |
| Q | 4.90 | 5.10 |
| R | 3.35 | 3.45 |
| S | 1.995 | 2.100 |
| U | 5.90 | 6.20 |
| Y | 9.90 | 10.10 |

isc Silicon PNP Darlington Power Transistor**2STW200****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | MAX | UNIT |
|----------------|--------------------------------------|--------------------------------------|-----|-------|---------------|
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage | $I_C=-50\text{mA}, I_B=0$ | -80 | | V |
| $V_{CE(sat)1}$ | Collector-Emitter Saturation Voltage | $I_C=-5\text{A}, I_B=-20\text{mA}$ | | -1.2 | V |
| $V_{CE(sat)2}$ | Collector-Emitter Saturation Voltage | $I_C=-10\text{A}, I_B=-40\text{mA}$ | | -1.75 | V |
| $V_{CE(sat)3}$ | Collector-Emitter Saturation Voltage | $I_C=-20\text{A}, I_B=-80\text{mA}$ | | -3.5 | V |
| $V_{BE(sat)}$ | Base-Emitter Saturation Voltage | $I_C=-20\text{A}, I_B=-80\text{mA}$ | | -3.3 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | $I_C=-10\text{A}; V_{CE}=-3\text{V}$ | | -3.0 | V |
| I_{CBO} | Collector Cutoff Current | $V_{CB}=-80\text{V}, I_E=0$ | | -50 | μA |
| I_{CEO} | Collector Cutoff Current | $V_{CE}=-80\text{V}, I_B=0$ | | -50 | μA |
| I_{EBO} | Emitter Cutoff Current | $V_{EB}=-5\text{V}; I_C=0$ | | -2 | mA |
| h_{FE-1} | DC Current Gain | $I_C=-5\text{A}; V_{CE}=-3\text{V}$ | 600 | 15000 | |
| h_{FE-2} | DC Current Gain | $I_C=-10\text{A}; V_{CE}=-3\text{V}$ | 500 | 12000 | |
| h_{FE-3} | DC Current Gain | $I_C=-20\text{A}; V_{CE}=-3\text{V}$ | 300 | 6000 | |